Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L1	3564	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 14:58
L2	1831	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER CLM.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 14:58
L3	49	((INLET OUTLET) NEAR3 PORTION) WITH (GAS LIQUID) WITH CHAMBER WITH CIRCULAR.CLM.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:23
L4	1	10/706415	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:33
L5	479	transistor with gate with ((si silicon) near3 containing)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:38
L6	96	5 and (dielectric with ((si silicon) near3 containing))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/08 15:39

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49 p US	2001121	Spot-implant method for	438/525			Wasshuber,	
200100	51413	MOS transistor application	į			Christoph	
50 115	2001111			257/F20 1	[KOBAVAŠHI	

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49	-	r U	S	2001121		Spot-implant method for	438/525			Wasshuber,	_	_		-		- -
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50	-	r U	S	2001111			257/314	257/E29.1		KOBAYASHI,	Е	-	_	FĪ	-	- -
* 72	1	1120	01004025	5		DEVICE HAVING NON	i 	65:	1 1 1	TAKASHI et al.	'			1	1 1	1
51	_	r U	S	2001091		METHODS OF	438/201	257/E21.6		KELLER, J.	_	-	_		- 1	
	1	120	01002154		1	ENHANCING DATA RE	: }	82:		DENNIS et al.	'	Li				
52	5	_ U	S 6864125	2005030		Process for growing a	438/142	427/255.27	1	Sandhu; Gurtej	_	_	_	-	- :	г г.
	l	B	2	.8	i i !	dielectric layer on a silico	: }	j.	; ! !	Sinoh et al		1 1	1	1 [1	
53	_	_ U	S 6844234	2005011		Semiconductor device	438/287	438/591;	1	Eguchi; Kazuhiro et	_	-	г	_	_ !	
	ļ <u>.</u>	В		8		and method for manufact	• • •	438/780:	 	al.				<u>[</u>		
54	,	_ U	5 6835983	2004122		Silicon-on-insulator	257/347	257/348;	1	Ning; Tak H. et al.	г	_	г	_	- i	r r.j.
	ļ	!B	2	;8		(SOI) integrated circuit (I	} :	257/349:	! ! !		:	١ ،	١ :	1 1	1	
55	٦	L U	2 S 6821825	2004112	33	Process for deposition of	438/150	117/88;	1	Todd; Michael A. et	5	_	г	-	<u>.</u> ا	- -
		B)	.3	!	semiconductor films		427/248.1:	ļ	[al						
56	٦	L U	8 6815296	2004110	22	Polysilicon back-gated	438/283	257/347;		Dennard; Robert H.	P	-		-	E i	
	1	B	2	9	1	SOI MOSFET for dynami		257/349:		et al.						:
57	٦	L U	S 6812527	2004110	20	Method to control device	257/347	257/348;		Dennard; Robert H.	5	_	г	-	- 1	r r
	١.	l B)	12		threshold of SOI MOSFE		257/351:		et al.		ļi				
58	_	L U	\$ 6808981	2004102	23	Method for fabricating	438/243	,		Mandelman; Jack	무	_	Г	г	r !	r r
	l	B	2	6		6F2 trench DRAM cell w		İ	ļ	A. et al.		Ĺ;				
59	l٦	LU	S 6790374	2004091	12	Plasma etch method for	216/37	134/1.1;		Ho; Kwok Keung	F	Г	r.	-	r !	ក∫ក∭៌
, j'a = -		В	l	4		forming plasma etched sil		134/1.2:		Paul et al.	ļ			<u> </u>		
60	_	r U	S 6777298	2004081			438/301	438/303;	1	Roy; Ronnen A. et	F	_	г	Г	-	r r 🖔
ļ	ļ	B		.7		disposable spacer CMOS		438/305.	ļ	al.	Ĺ	1	1		1	:
61	_	_ U	S 6764902	2004072	28	Method of manufacturing	1438/257	438/775:		Kobavashi: Takashi	ļ. .	-	٠.	إرجا	بأج	لغرواج
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55		US 6821825	2004112	33	Process for deposition of	438/150	117/88;		Todd; Michael A. et	5					г.
-		B2	13		semiconductor films		427/248.1:		al,	۳	'	j	<u>' '</u>	i'	
56		US 6815296	2004110	22	Polysilicon back-gated	438/283	257/347;		Dennard; Robert H.	D	_	-	- 1	- -	Г
		B2	9		SOI MOSFET for dynami	; }	257/349:		et al.	L			`	1.	1
57	r r	US 6812527	2004110	20	Method to control device	ė.	257/348;		Dennard; Robert H.	F	Г	r	- 1	- -	п.
	ļ	B2	2		threshold of SOI MOSFE		257/351:		et al.				↓.		
58 :		US 6808981	2004102		:	438/243		1	Mandelman; Jack	Þ	Г.	r.	r	rjr	· m
		B2	6	ļ	6F2 trench DRAM cell w		1		A. et al.	L			‡.		
59		US 6790374	2004091		Plasma etch method for	i	134/1.1;		Ho: Kwok Keung	Þ	r.	п	Г	רור	п
-	ļ <u></u>	B1	4	22	forming plasma etched sil		134/1.2:		Paul et al.						
60		US 6777298	2004081	22	:	438/301	438/303;	1	Roy; Ronnen A. et	Þ	п	г	E I	r ir	П
61	ł	B2 US 6764902	2004072	20	disposable spacer CMOS		438/305:		al. Kohawashi, Takashi		ļ}				
01	ГГ	03 0704902	2004072	20	Method of manufacturing	1430/23/	438/775;		Kobayashi; Takashi	F.	Г	Г.	rin	r. r	L F

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438/710

438/233

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257/303: 257/E21.2

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Plasma etch method for

Semiconductor device

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Fabricating an embedded 257/295

Multi-layered polysilicon 438/592

Silicate gate dielectric

et al. Cartier; Eduard

Albert et al. Moise; Ted et al.

Yang: Szu-Hung et

Wieczorek; Karsten

Clark, Jr.; William

Grider: Douglas T

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,	US 6620719 BL	6	Method of forming ohmic contacts using a self dooi		257/E21.4 13:	1 1	Andry; Paul Stephen et al.	F	пгг	г г.
60	11S 6607946	12003081 15	Process for growing a	438/142	257/F21 1		Sandhu: Gurtei	1 1		: :

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68	r	٦ ار	JS 6620719	2003091	14	Method of forming ohmic	4	257/E21.4		Andry; Paul	무	г	г	г	г	-
		[E		6	ļ	contacts using a self dooi		13:		Stephen et al.		ļ		ļļ]	
69	r l	r I	JS 6607946	2003081			;	257/E21.1	į	Sandhu; Gurtej	Þ	n	п	r	r r	- [-]
		[E	31	9	ļ	dielectric laver on a silico		93:		Singh et al.				<u> </u>]	
70	r		JS 6596648	2003072	1	Material removal method	438/745	257/E21.0		Wu; Zhiqiang et al.	Þ	n	п	г	ГГ	- [=]
			32	2		for forming a structure	420/257	11:				,Ì		 +		
71.	r	г. [JS 6596585	2003072		Method of manufacturing	438/25/	257/E29.1		Kobayashi; Takashi	F	Г	r,	٦	Г	- 🕝
		<u>:</u> <u> </u>	32	2	ļ	semiconductor device		65:	ļ	et al.				}÷		
72	-	r.	JS 6566210	2003052	8	Method of improving gate	4	257/344;		Ajmera; Atul C. et	Þ	r.	п	r.	r	- [E!]
		;E	32	0	ļ	activation by employing a		257/E21.1		al.		ļ		ļļ		
73	_	ا ا	JS 6548874	2003041		Higher voltage transistors	<u> </u>	257/344;		Morton; Alec et al.	₽.	п	П	г	רור	- [ករុំ
1.		!E	31	5		for sub micron CMOS or		257/408:]		11	. 	
74	P	٦ار	JS 6521963	2003021	35	Semiconductor device	257/412	257/324;		Ota; Kazunobu et	г	r.	г	г	r. Ir	- nii
*	!	E	31	8		and method of manufactu	: }	257/350:	Ì	al.		ıi		LL	<u></u>	.1.5
75 .	P	٦ ر	JS 6514843	2003020	8	Method of enhanced	438/595	257/E21.3		Dokumaci; Omer et	г	г	г	г	r. r	
	1	F	32	4	i	oxidation of MOS transist		35:	1	al.						
76	p	_ [JS 6489649	2002120	29			257/315;		Kobayashi; Takashi	г	Г	г	_	r ir	- 6
		Ε	32	3	1	having nonvolatile memo		257/316:		et al.						
77 .	p	, I	JS 6469350	2002102	13	Active well schemes for	257/349	257/347;		Clark, Jr.; William	г	r	г	-	г. г	- п
	٠	E	31	2		SOI technology		257/354:		F. et al.	•		•		, ļ.	1
78		_ [JS 6462403	2002100	12		257/640	257/350;		Uochi; Hideki	г	_	_	-	r r	- -
91		F	31	8		comprising thin film trans		257/59:	1		!'	, ' · · !	•	١'''	, ;	13
79 .		_ [JS 6458666	2002100	5	Spot-implant method for		438/525;	ļ	Wasshuber;	F	_	Γ.	_	- ,	- -
-9.4		E	32	1		MOS transistor applicatio		438/531	İ	Christoph	<u> </u>				<u>' l'</u>	
80	,,	_ [[JS 6444584	2002090	10	Plasma etch method for	438/706	438/710:		Hsiao: Yung-Kuan	-,	, ,)	, ,	[-]	5	
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83					575	2002043	16	Treatment of etching	216/67	134/1.1;		Yin; Gerald Zheyao	F	_	· F	-	- 1	- Г.
				В1		0	ļ	chambers using activated		438/727: 4		et al.	:		:	1 1	:	i
84	- 1,	7	г.	US 6352	900	2002030	5	Controlled oxide growth	438/305			Mehrotra; Manoj et	_	_	г	Г	г і	- -
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85	-	P	г	US 6251	729	2001062	9	Method of manufacturing	438/257			Montree; Andreas	٦	г	г	г	r r	- Г.
86				BL	701	6 2001030	-	a nonvolatile memory	438/763	257/206:		H. et al.	ļ			}÷		
80		P	Г.	02 013/	/01	2001030	9	Lightly nitridation	;	257/E21.2		Shue; Shau-Lin et	Г	г	Γ:	Г	ר	г г.
87	-			BL	303	2001012	6	surface for preparing thin Method of manufacturing	438/194	68: 257/E21.4		aı. Schmitz; Jurriaan et				1+		
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88	7			US 6133	620	2000101	10	Semiconductor device	257/649			Uochi; Hideki	†	_		121		
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89		,	_	US 6124	638	2000092	47	Semiconductor device	257/751	257/384;		Iwasa; Shoichi	-	_	_	_	г : r	- r
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90	-	P :	г	US 5897	345	1999042	10	Semiconductor device	438/151	257/E21.2		Uochi; Hideki	г	г	г.	-	rir	r r
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91		P	Γ.	US 5/31	238	1998032	8	Integrated circuit having				Cavins; Craig Allan	г	٦	Г	г	רוְּׁוֹ	- r.
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92		Þ	Γ.	US 4894	UYJ	1990011	12	Single-polysilicon dram	237/311	257/384; 257/915;		Tigelaar; Howard L. et al.	Г	٦	Г	-	Г	- r
93				A US 4811	078	1989030	20	device and process Integrated circuit device	257/311			er al. Tigelaar; Howard L.	 -	l	ļ	1		
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94	7			US 4811	076	1989030	111	Device and process with				Tigelaar; Howard L.	-	_				_ _
- •		۲	f.	A	•	7		doubled capacitors		257/315:	1 !	et al.	ì	ì	1	1 1	i	استبا
95	\Box	-		US 4810	673	1989030	9	Oxide deposition method	438/386			Freeman: Dean W.] -	-		[-]	,	يز _ [_

et al. Tigelaar; Howard L. et al. Freeman: Dean W.